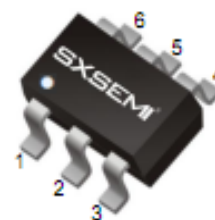
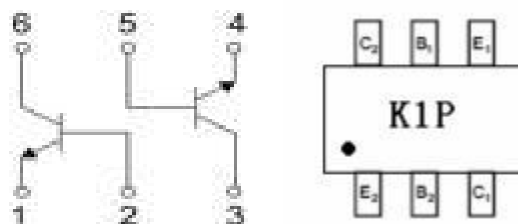


SOT-363



MARKING: K1P



FEATURE

Complementary PNP Type available MMDT2907A

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_C	Collector Power Dissipation	200	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	$-55\sim+150$	$^{\circ}\text{C}$

Switching characteristics

Parameter	Symbol	Test conditions	Min	Max	Unit
Delay time	t_d	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $V_{BE(off)}=0.5\text{V}$, $I_{B1}=15\text{mA}$		10	ns
Rise time	t_r			25	ns
Storage time	t_s	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_{B1}=-I_{B2}=15\text{mA}$		225	ns
Fall time	t_f			60	ns

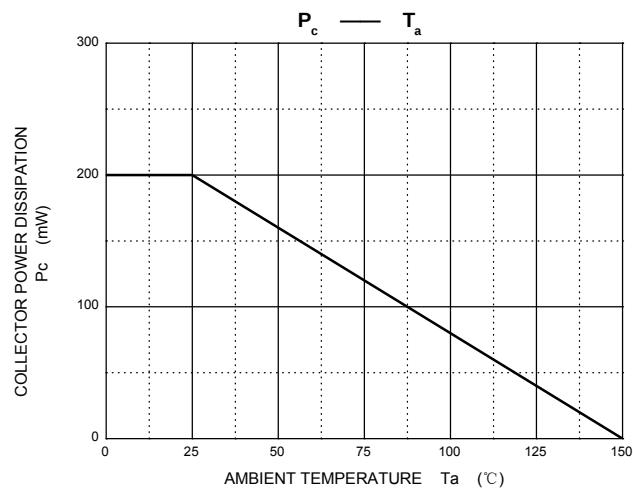
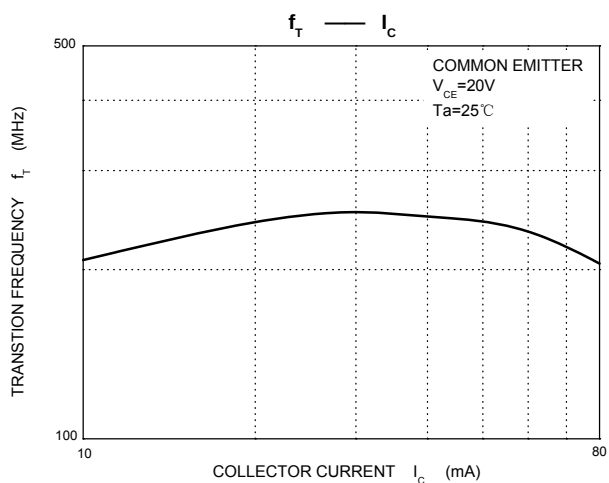
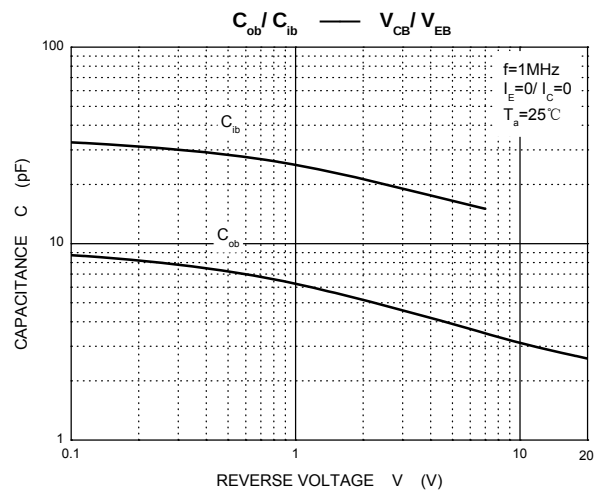
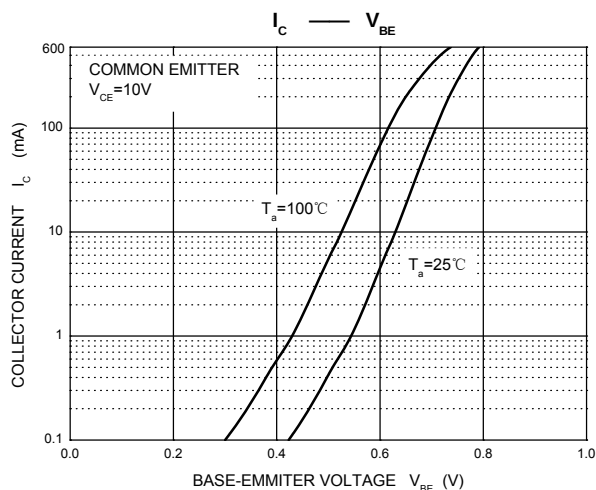
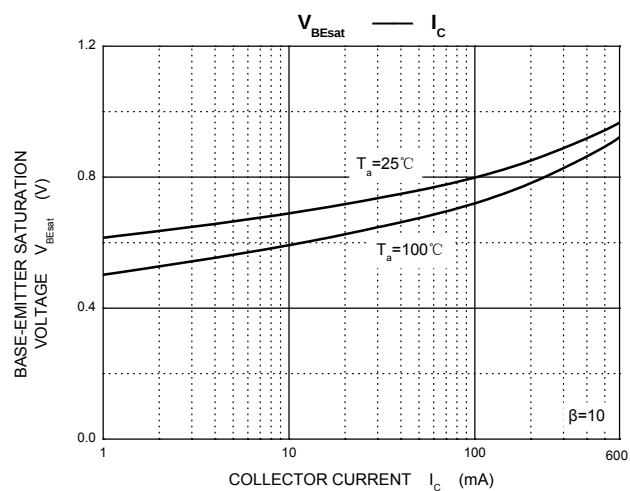
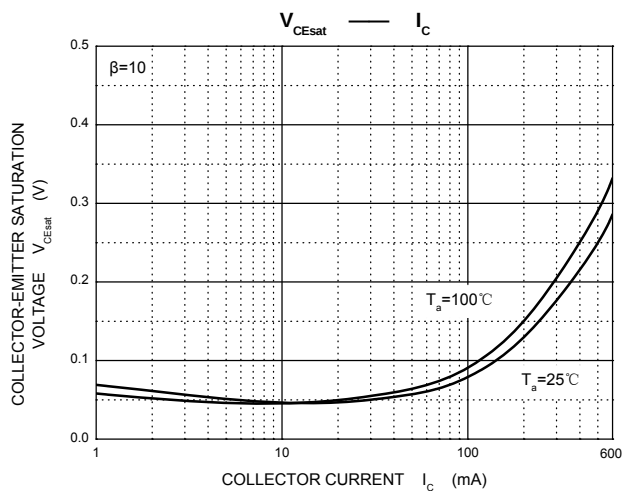
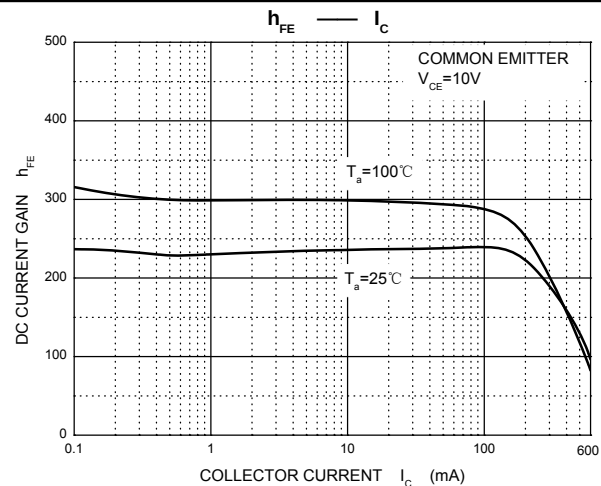
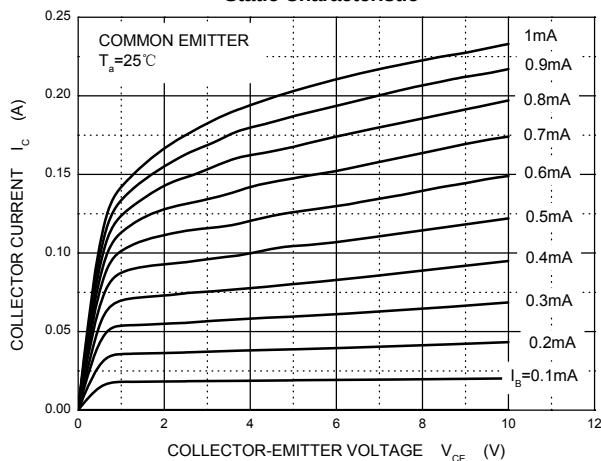
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	75		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 60V, I_E = 0$		10	nA
Collector cut-off current	I_{CEX}	$V_{CE} = 60V, V_{EB(off)} = 3V$		10	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3V, I_C = 0$		10	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = 10V, I_C = 0.1mA$	35		
	$h_{FE(2)}$	$V_{CE} = 10V, I_C = 1mA$	50		
	$h_{FE(3)}$	$V_{CE} = 10V, I_C = 10mA$	75		
	$h_{FE(4)}$	$V_{CE} = 10V, I_C = 150mA$	100	300	
	$h_{FE(5)}$	$V_{CE} = 10V, I_C = 500mA$	40		
	$h_{FE(6)}$	$V_{CE} = 1V, I_C = 150mA$	35		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = 150mA, I_B = 15mA$		0.3	V
	$V_{CE(sat)2}$	$I_C = 500mA, I_B = 50mA$		1	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C = 150mA, I_B = 15mA$	0.6	1.2	V
	$V_{BE(sat)2}$	$I_C = 500mA, I_B = 50mA$		2	V
Transition frequency	f_T	$V_{CE} = 20V, I_C = 20mA, f = 100MHz$	300		MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		8	pF
Input Capacitance	C_{ib}	$V_{EB} = 0.5V, I_C = 0, f = 1MHz$		25	pF
Noise Figure	NF	$V_{CE} = 10V, I_C = 100\mu A, f = 1KHz, R_s = 1K\Omega$		4	dB

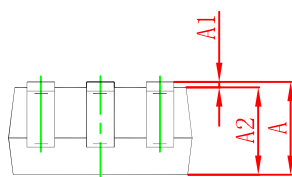
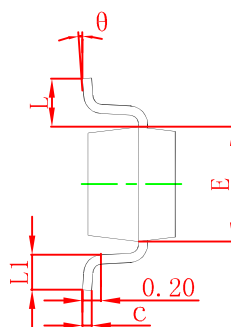
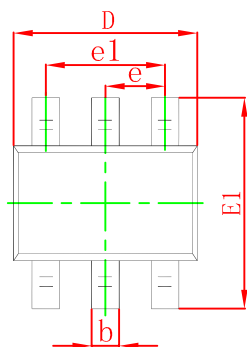
Typical Characteristics

DUAL TRANSISTOR (NPN+NPN)

Static Characteristic

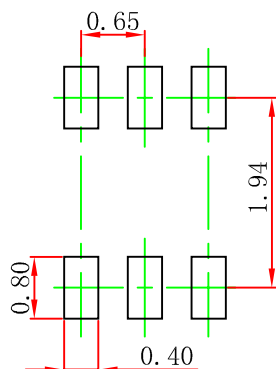


SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.